



2SD1437

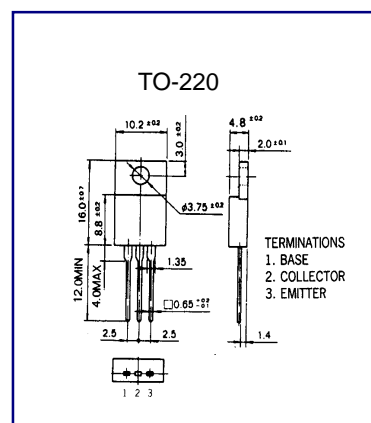
NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SB1033

ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

| Characteristic | Symbol | Rating | Unit |
|--|------------------|---------|------|
| Collector-Base Voltage | V _{CB0} | 80 | V |
| Collector-Emitter Voltage | V _{CEO} | 60 | V |
| Emitter-Base voltage | V _{EB0} | 5 | V |
| Collector Current (DC) | I _C | 3 | A |
| Collector Dissipation (T _c =25°C) | P _C | 40 | W |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature | T _{stg} | -50~150 | °C |



ELECTRICAL CHARACTERISTICS (T_A=25°C)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|---------------------------------------|----------------------|---|-----|-----|-----|------|
| Collector Cutoff Current | I _{CBO} | V _{CB} = 80V , I _E =0 | | | 100 | μA |
| Emitter Cutoff Current | I _{EB0} | V _{EB} =5V , I _C =0 | | | 100 | μA |
| DC Current Gain | h _{FE1} | V _{CE} = 5V , I _C =1A | | 120 | | |
| Collector- Emitter Saturation Voltage | V _{CE(sat)} | I _C =2A , I _B =0.2A | | | 1.0 | V |
| Current Gain Bandwidth Product | f _T | V _{CE} = 5V , I _C =0.5A | | 8 | | MHZ |